

2MBI300UE-120



IGBT Module U-Series 1200V / 300A 2 in one-package

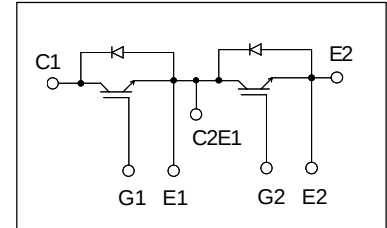
■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Equivalent Circuit Schematic



■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item		Symbol	Conditions	Rating	Unit	
Collector-Emitter voltage		V _{CES}	1200		V	
Gate-Emitter voltage		V _{GES}	±20		V	
Collector current		I _c	Continuous	T _c =25°C	450	A
				T _c =80°C	300	
		I _{cp}	1ms	T _c =25°C	900	
				T _c =80°C	600	
		-I _c			300	
		-I _c pulse			600	
Collector Power Dissipation		P _c	1 device	1660	W	
Junction temperature		T _j	+150		°C	
Storage temperature		T _{stg}	-40 to +125			
Isolation voltage	between terminal and copper base *1		V _{iso}	AC:1min.	2500	VAC
Screw Torque		Mounting *2		3.5	N·m	
		Terminals *2		4.5		

*1 : All terminals should be connected together when isolation test will be done.

*2 : Recommendable value : Mounting 2.5 to 3.5 N·m(M5 or M6), Terminals 3.5 to 4.5N·m(M6)

● Electrical characteristics (at T_j=25°C unless otherwise specified)

Item	Symbols	Conditions		Characteristics			Unit
				Min.	Typ.	Max.	
Zero gate voltage collector current	ICES	VGE=0V, VCE=1200V		—	—	3.0	mA
Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V		—	—	600	nA
Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=300mA		4.5	6.5	8.5	V
Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V, IC=300A	TJ=25°C	—	1.95	2.30	V
			TJ=125°C	—	2.20	—	
	VCE(sat) (chip)		TJ=25°C	—	1.75	2.10	
			TJ=125°C	—	2.00	—	
Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz		—	34	—	nF
Turn-on time	ton	VCC=600V IC=300A VGE=±15V		—	0.36	1.20	μs
	tr			—	0.21	0.60	
	tr(j)			—	0.03	—	
Turn-off time	toff	RG=2.0 Ω		—	0.37	1.00	
	tr			—	0.07	0.30	
Forward on voltage	VF (terminal)	VGE=0V IF=300A	TJ=25°C	—	1.75	2.05	V
			TJ=125°C	—	1.85	—	
	VF (chip)		TJ=25°C	—	1.60	1.90	
			TJ=125°C	—	1.70	—	
Reverse recovery time	trr	IF=300A		—	—	0.35	μs
Lead resistance, terminal-chip*3	R lead			—	0.45	—	mΩ

*3:Biggest internal terminal resistance among arm.

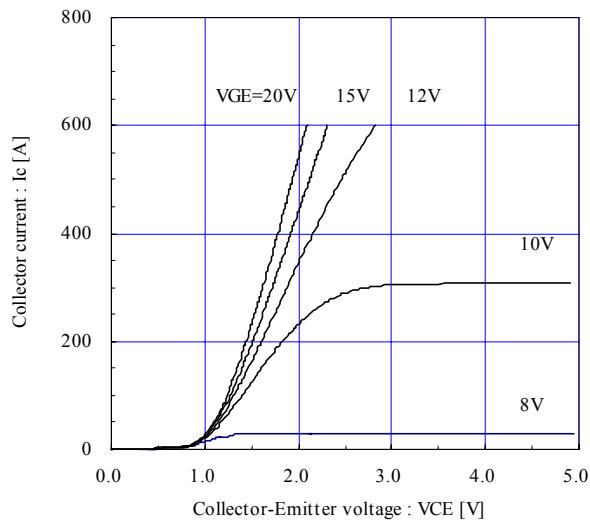
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	R _{th(j-c)}	IGBT	—	—	0.075	°C/W
	R _{th(j-c)}	FWD	—	—	0.12	°C/W
Contact Thermal resistance	R _{th(c-f)} *4	With thermal compound	—	0.0167	—	°C/W

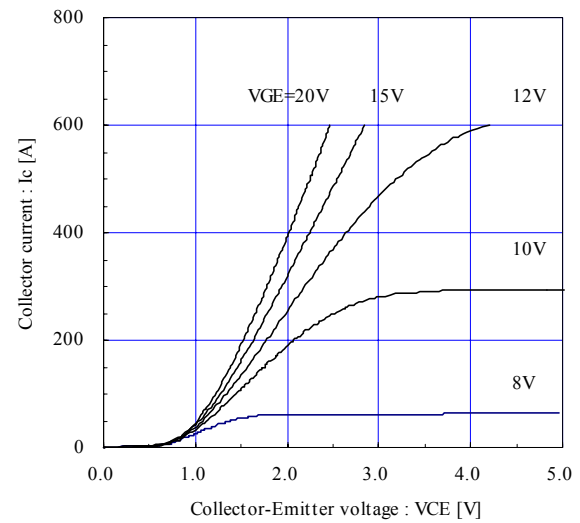
*4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

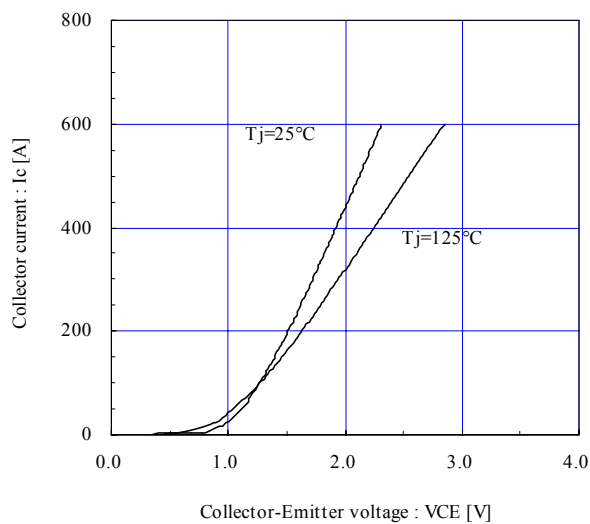
Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

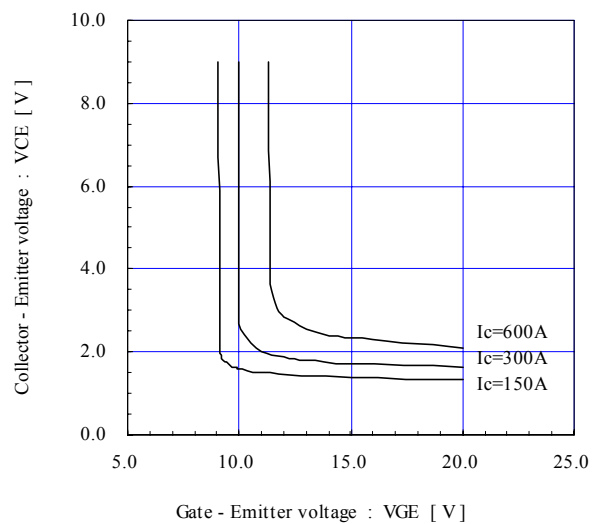
Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 125^\circ\text{C}$ / chip

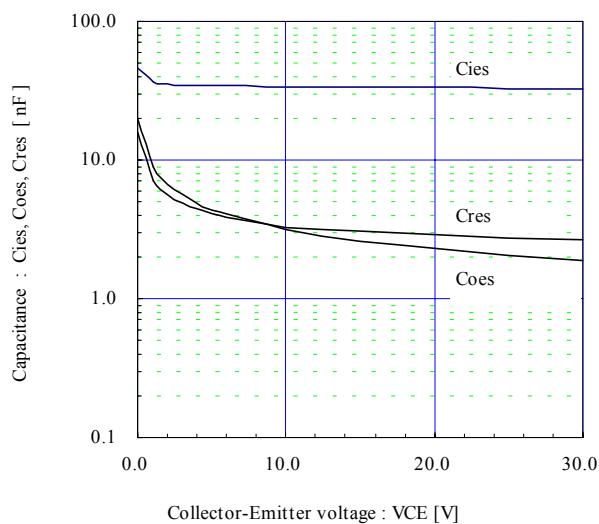
Collector current vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 15\text{V}$ / chip

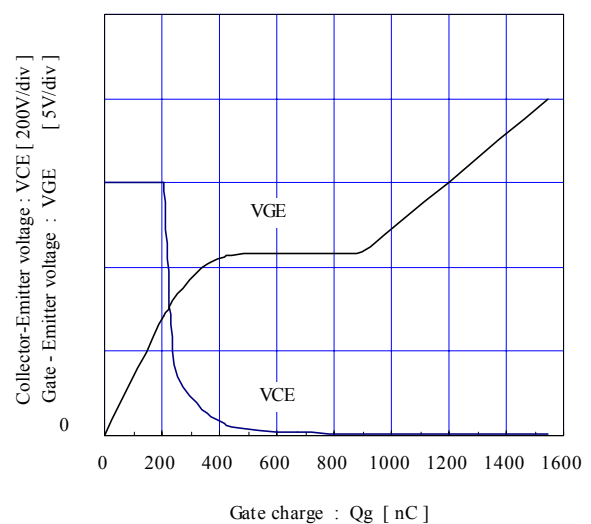
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

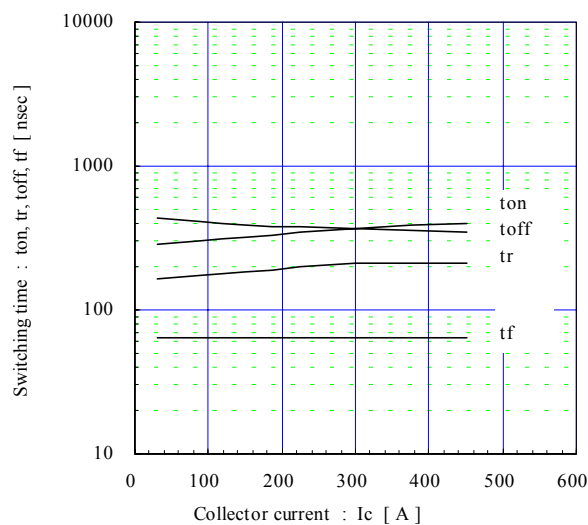
Capacitance vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$ 

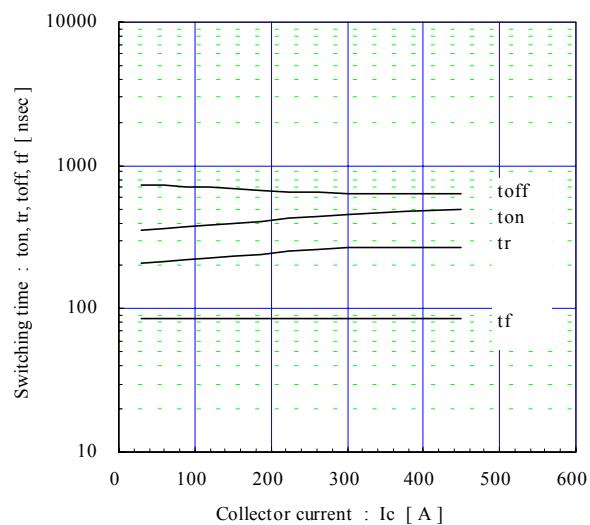
Dynamic Gate charge (typ.)

 $V_{cc} = 600\text{V}$, $I_c = 300\text{A}$, $T_j = 25^\circ\text{C}$ 

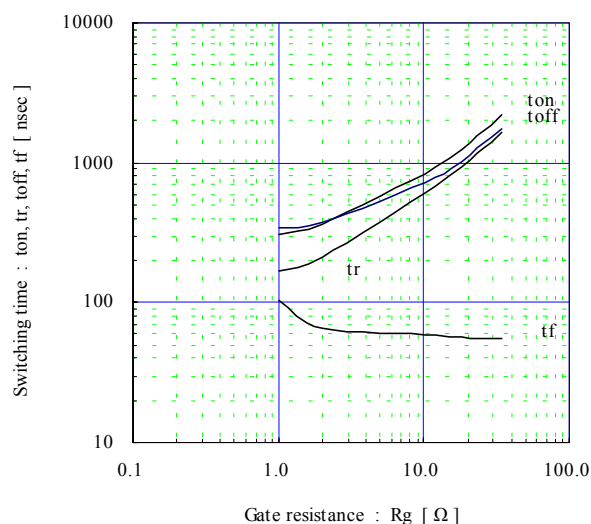
Switching time vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=2\Omega, T_j=25^\circ C$ 

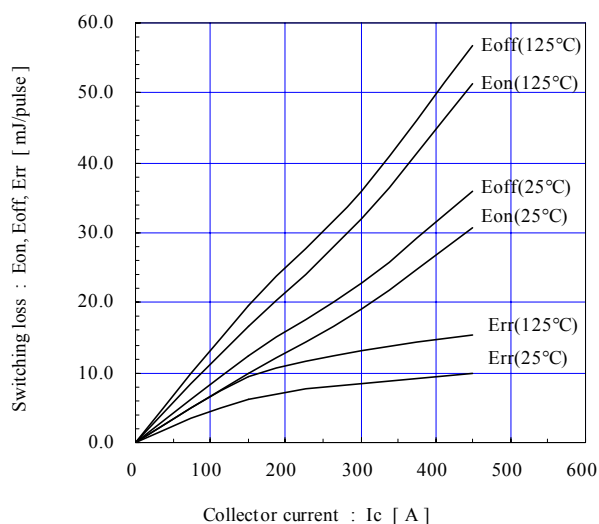
Switching time vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=2\Omega, T_j=125^\circ C$ 

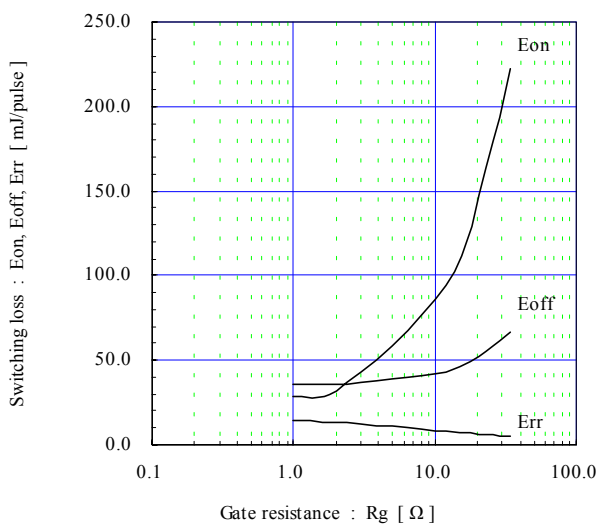
Switching time vs. Gate resistance (typ.)

 $V_{cc}=600V, I_c=300A, V_{GE}=\pm 15V, T_j=25^\circ C$ 

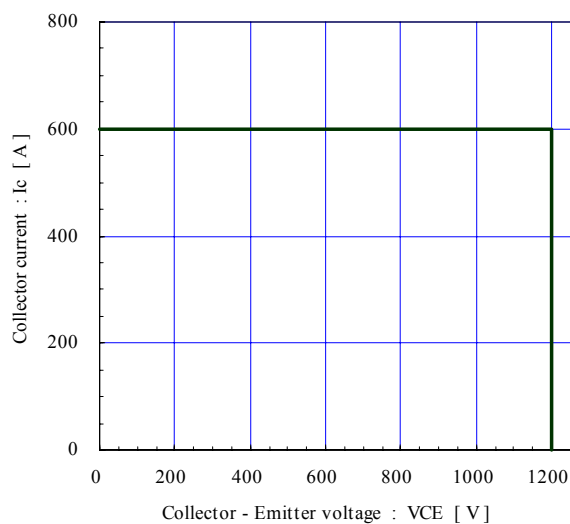
Switching loss vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=2\Omega$ 

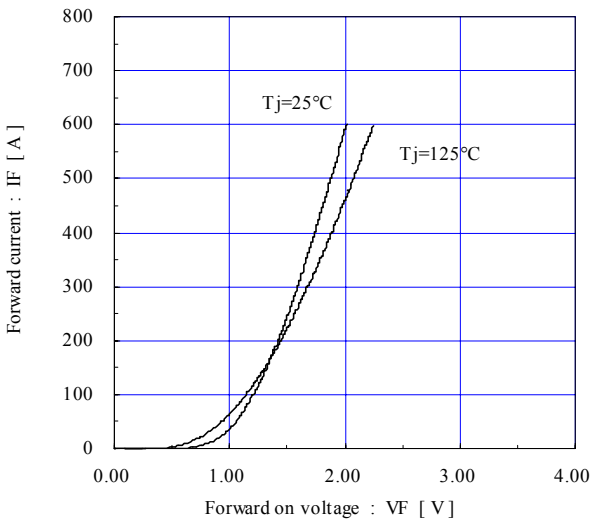
Switching loss vs. Gate resistance (typ.)

 $V_{cc}=600V, I_c=300A, V_{GE}=\pm 15V, T_j=125^\circ C$ 

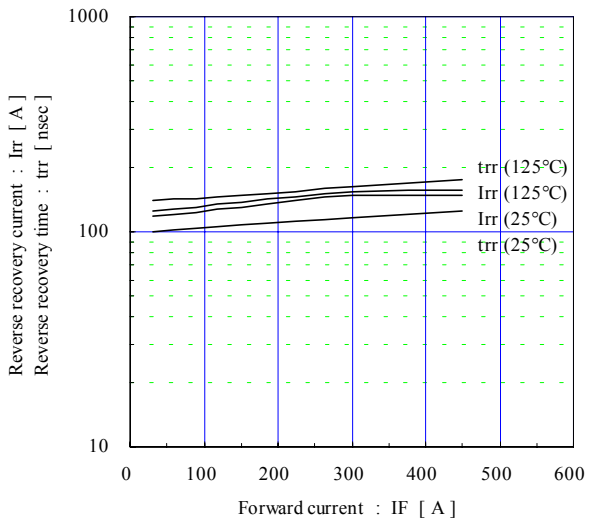
Reverse bias safe operating area (max.)

 $+V_{GE}=15V, -V_{GE} \leq 15V, R_g \geq 2\Omega, T_j \leq 125^\circ C$ 

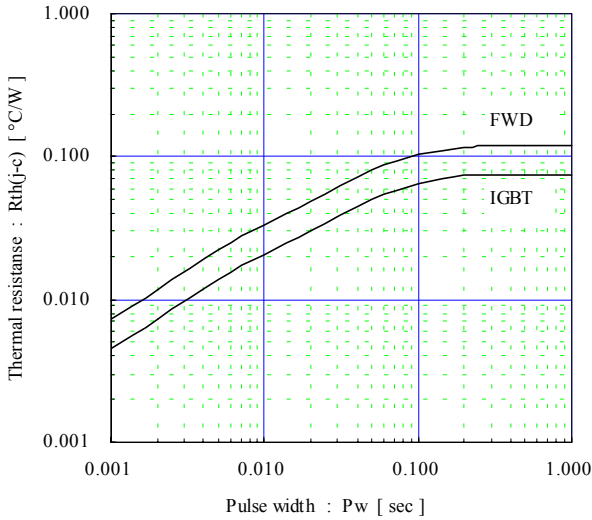
Forward current vs. Forward on voltage (typ.)
chip



Reverse recovery characteristics (typ.)
Vce=V, VGE=±15V, Rg=2Ω



Transient thermal resistance (max.)



■ Outline Drawings, mm

